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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	22
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-WFQFN Exposed Pad
Supplier Device Package	32-HWQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101baana-u0

Table 1-1. List of Ordering Part Numbers

(9/12)

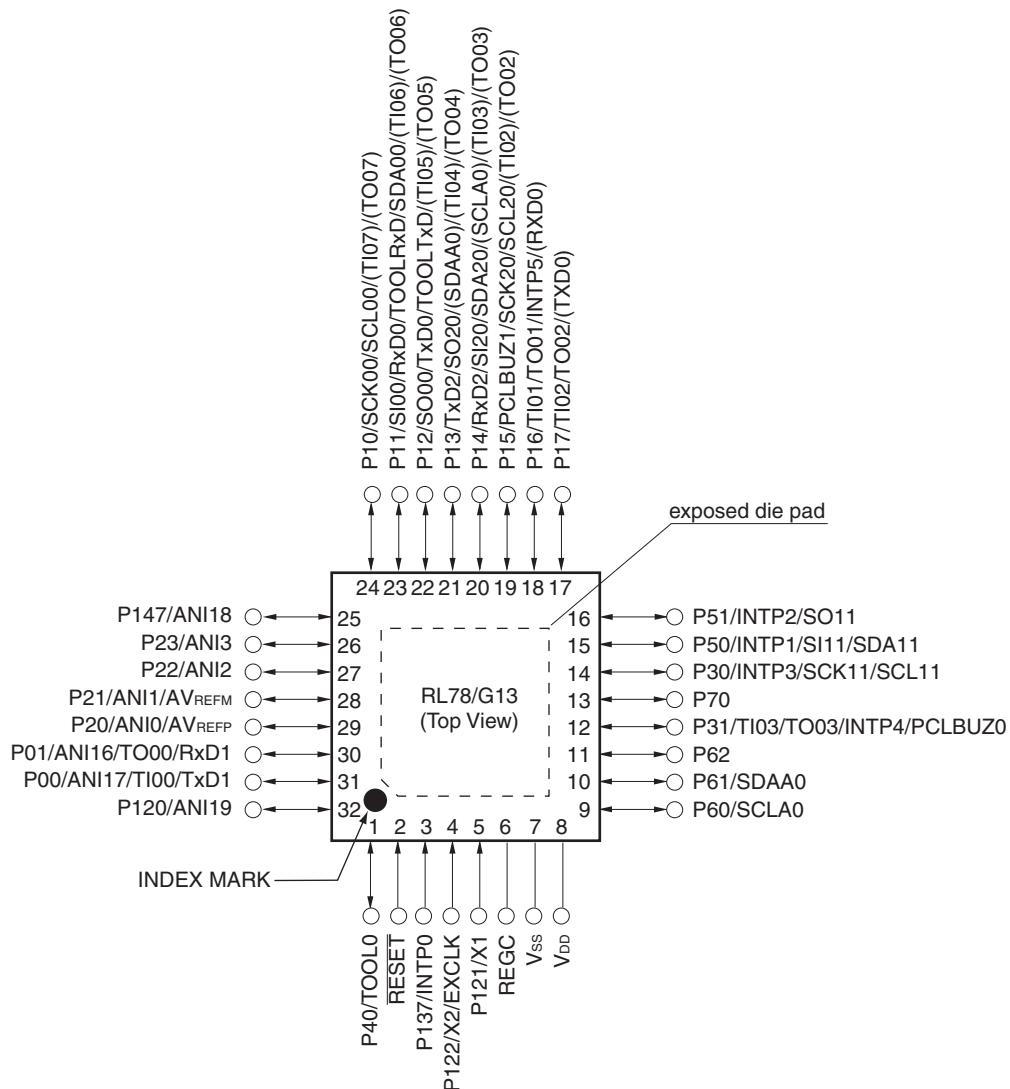
Pin count	Package	Data flash	Fields of Application <small>Note</small>	Ordering Part Number
64 pins	64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)	Mounted	A	R5F100LCAB#V0, R5F100LDAB#V0, R5F100LEAB#V0, R5F100LFAB#V0, R5F100LGAB#V0, R5F100LHAB#V0, R5F100LJAB#V0, R5F100LKAB#V0, R5F100LLAB#V0 R5F100LCAB#X0, R5F100LDAB#X0, R5F100LEAB#X0, R5F100LFAB#X0, R5F100LGAB#X0, R5F100LHAB#X0, R5F100LJAB#X0, R5F100LKAB#X0, R5F100LLAB#X0 R5F100LCD#V0, R5F100LDD#V0, R5F100LED#V0, R5F100LFDF#V0, R5F100LGDF#V0, R5F100LHD#V0, R5F100LJD#V0, R5F100LKDF#V0, R5F100LLD#V0 R5F100LCD#X0, R5F100LDD#X0, R5F100LED#X0, R5F100LFDF#X0, R5F100LGDF#X0, R5F100LHD#X0, R5F100LJD#X0, R5F100LKDF#X0, R5F100LLD#X0 R5F100LCGFB#V0, R5F100LDGFB#V0, R5F100LEGFB#V0, R5F100LFGFB#V0 R5F100LCGFB#X0, R5F100LDGFB#X0, R5F100LEGFB#X0, R5F100LFGFB#X0 R5F100LGGFB#V0, R5F100LHGFB#V0, R5F100LJGFB#V0 R5F100LGGFB#X0, R5F100LHGFB#X0, R5F100LJGFB#X0
			D	
			G	
			A	R5F101LCAB#V0, R5F101LDAB#V0, R5F101LEAB#V0, R5F101LFAB#V0, R5F101LGAB#V0, R5F101LHAB#V0, R5F101LJAB#V0, R5F101LKAB#V0, R5F101LLAB#V0 R5F101LCAB#X0, R5F101LDAB#X0, R5F101LEAB#X0, R5F101LFAB#X0, R5F101LGAB#X0, R5F101LHAB#X0, R5F101LJAB#X0, R5F101LKAB#X0, R5F101LLAB#X0 R5F101LCD#V0, R5F101LDD#V0, R5F101LED#V0, R5F101LFDF#V0, R5F101LGDF#V0, R5F101LHD#V0, R5F101LJD#V0, R5F101LKDF#V0, R5F101LLD#V0 R5F101LCD#X0, R5F101LDD#X0, R5F101LED#X0, R5F101LFDF#X0, R5F101LGDF#X0, R5F101LHD#X0, R5F101LJD#X0, R5F101LKDF#X0, R5F101LLD#X0
			D	
	64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)	Mounted	A	R5F100LCABG#U0, R5F100LDABG#U0, R5F100LEABG#U0, R5F100LFABG#U0, R5F100LGABG#U0, R5F100LHABG#U0, R5F100LJABG#U0 R5F100LCABG#W0, R5F100LDABG#W0, R5F100LEABG#W0, R5F100LFABG#W0, R5F100LGABG#W0, R5F100LHABG#W0, R5F100LJABG#W0 R5F100LCGBG#U0, R5F100LDGBG#U0, R5F100LEGBG#U0, R5F100LFGBG#U0, R5F100LGBBG#U0, R5F100LHGBG#U0, R5F100LJGBG#U0 R5F100LCGBG#W0, R5F100LDGBG#W0, R5F100LEGBG#W0, R5F100LFGBG#W0, R5F100LGBBG#W0, R5F100LHGBG#W0, R5F100LJGBG#W0
			G	
			A	R5F101LCABG#U0, R5F101LDABG#U0, R5F101LEABG#U0, R5F101LFABG#U0, R5F101LGABG#U0, R5F101LHABG#U0, R5F101LJABG#U0 R5F101LCABG#W0, R5F101LDABG#W0, R5F101LEABG#W0, R5F101LFABG#W0, R5F101LGABG#W0, R5F101LHABG#W0, R5F101LJABG#W0
			Not mounted	

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.5 32-pin products

- 32-pin plastic HWQFN (5 × 5 mm, 0.5 mm pitch)



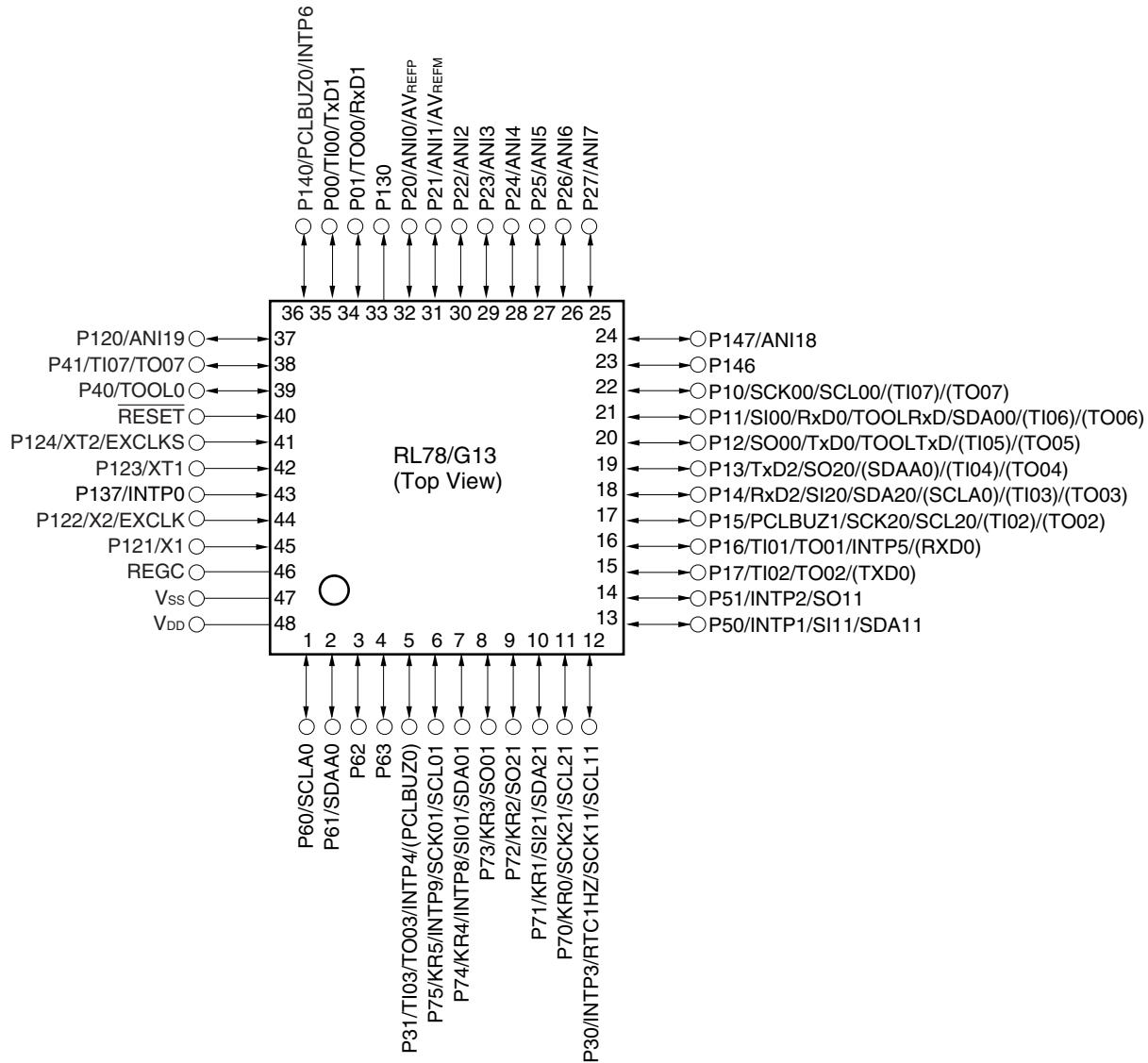
Caution Connect the REGC pin to V_{ss} via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.
3. It is recommended to connect an exposed die pad to V_{ss}.

1.3.9 48-pin products

- 48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)

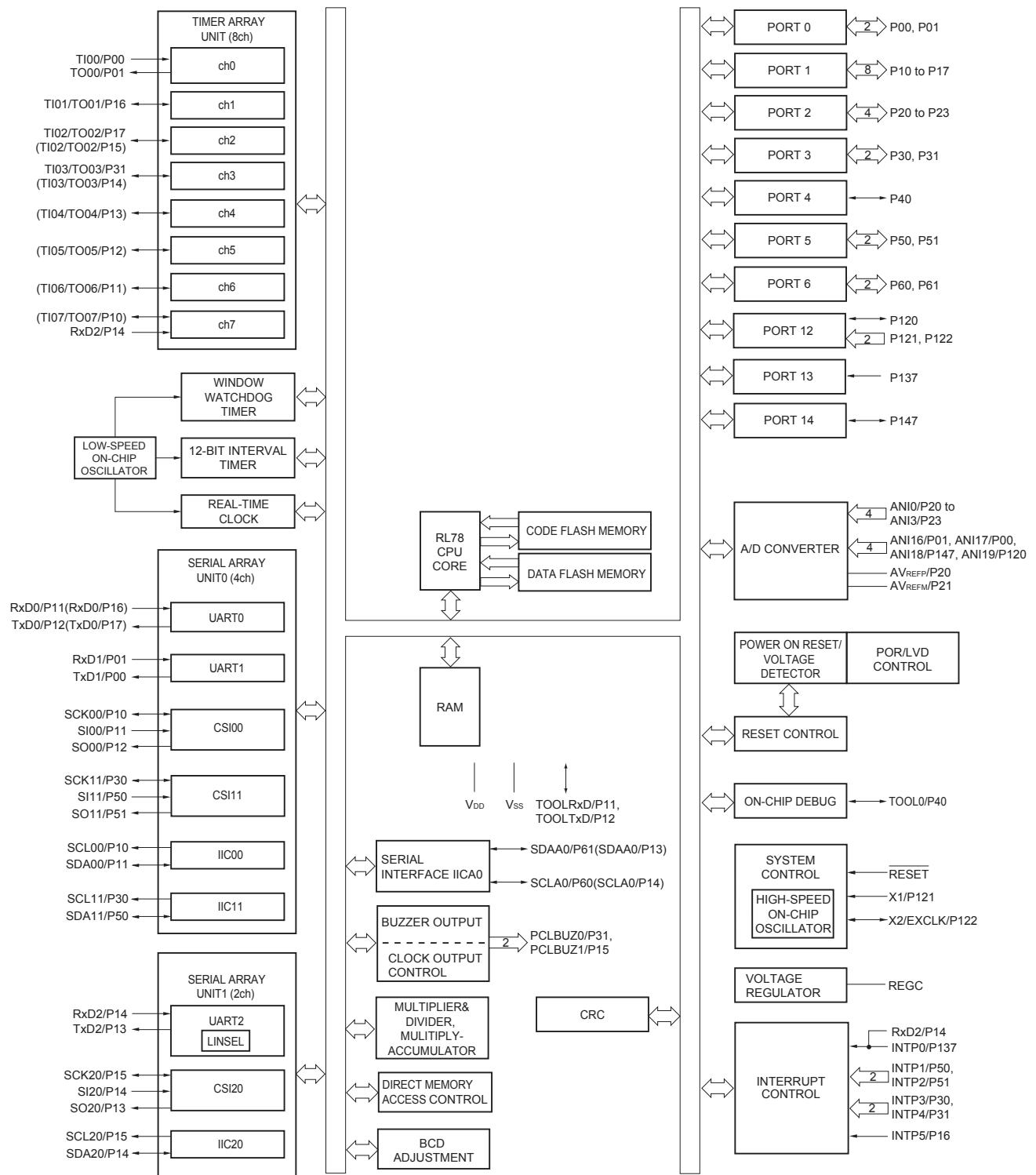


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.4 30-pin products



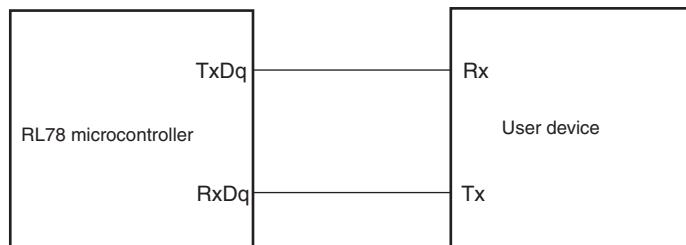
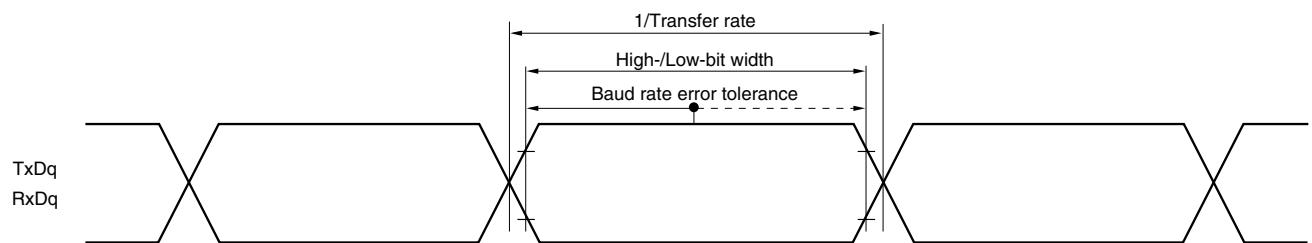
Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products

 $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{ss} = EV_{ss0} = EV_{ss1} = 0 \text{ V}$) (1/2)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current ^{Note 1}	I_{DD1}	Operating mode HS (high-speed main) mode ^{Note 5}	$f_{IH} = 32 \text{ MHz}$ ^{Note 3}	Basic operation	$V_{DD} = 5.0 \text{ V}$		2.6			mA
					$V_{DD} = 3.0 \text{ V}$		2.6			mA
			$f_{IH} = 24 \text{ MHz}$ ^{Note 3}	Normal operation	$V_{DD} = 5.0 \text{ V}$		6.1	9.5		mA
					$V_{DD} = 3.0 \text{ V}$		6.1	9.5		mA
		LS (low-speed main) mode ^{Note 5}	$f_{IH} = 16 \text{ MHz}$ ^{Note 3}	Normal operation	$V_{DD} = 5.0 \text{ V}$		3.5	5.3		mA
					$V_{DD} = 3.0 \text{ V}$		3.5	5.3		mA
		LV (low-voltage main) mode ^{Note 5}	$f_{IH} = 8 \text{ MHz}$ ^{Note 3}	Normal operation	$V_{DD} = 3.0 \text{ V}$		1.5	2.3		mA
					$V_{DD} = 2.0 \text{ V}$		1.5	2.3		mA
		HS (high-speed main) mode ^{Note 5}	$f_{MX} = 20 \text{ MHz}$ ^{Note 2} , $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		3.9	6.1		mA
					Resonator connection		4.1	6.3		mA
			$f_{MX} = 20 \text{ MHz}$ ^{Note 2} , $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		3.9	6.1		mA
					Resonator connection		4.1	6.3		mA
			$f_{MX} = 10 \text{ MHz}$ ^{Note 2} , $V_{DD} = 5.0 \text{ V}$	Normal operation	Square wave input		2.5	3.7		mA
					Resonator connection		2.5	3.7		mA
		LS (low-speed main) mode ^{Note 5}	$f_{MX} = 8 \text{ MHz}$ ^{Note 2} , $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		1.4	2.2		mA
					Resonator connection		1.4	2.2		mA
			$f_{MX} = 8 \text{ MHz}$ ^{Note 2} , $V_{DD} = 2.0 \text{ V}$	Normal operation	Square wave input		1.4	2.2		mA
					Resonator connection		1.4	2.2		mA
		Subsystem clock operation	$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = -40^\circ\text{C}$	Normal operation	Square wave input		5.4	6.5		μA
					Resonator connection		5.5	6.6		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +25^\circ\text{C}$	Normal operation	Square wave input		5.5	6.5		μA
					Resonator connection		5.6	6.6		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +50^\circ\text{C}$	Normal operation	Square wave input		5.6	9.4		μA
					Resonator connection		5.7	9.5		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +70^\circ\text{C}$	Normal operation	Square wave input		5.9	12.0		μA
					Resonator connection		6.0	12.1		μA
			$f_{SUB} = 32.768 \text{ kHz}$ ^{Note 4} $T_A = +85^\circ\text{C}$	Normal operation	Square wave input		6.6	16.3		μA
					Resonator connection		6.7	16.4		μA

(Notes and Remarks are listed on the next page.)

UART mode connection diagram (during communication at same potential)**UART mode bit width (during communication at same potential) (reference)**

Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

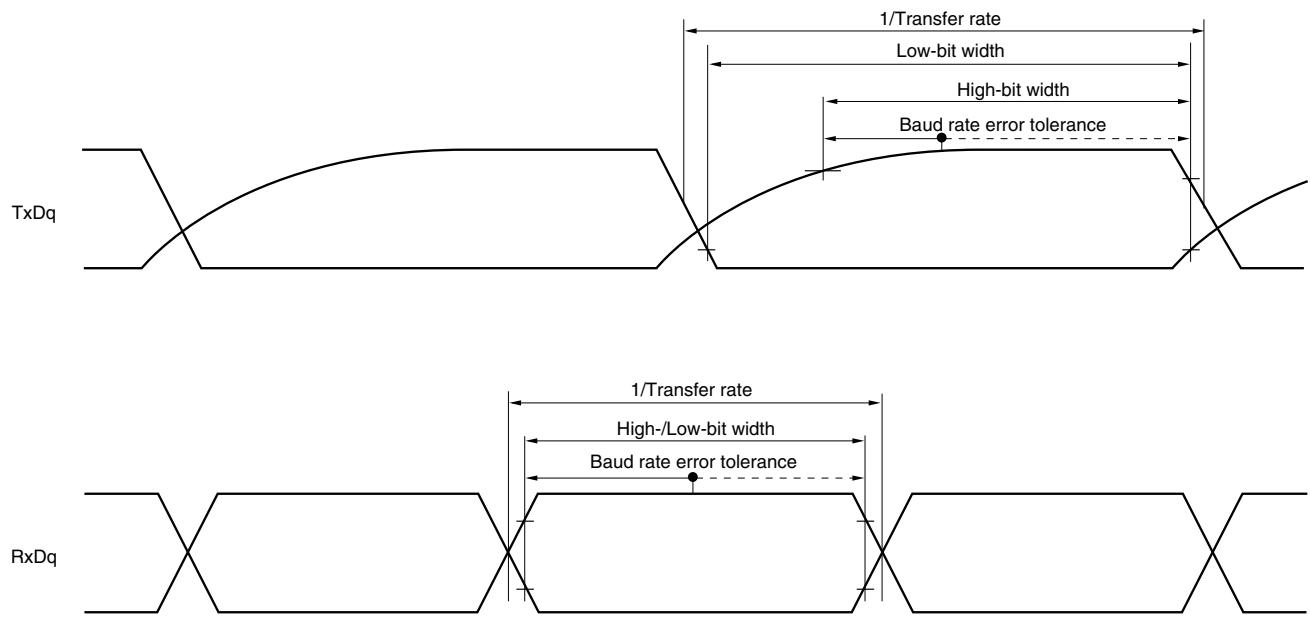
2. f_{MCK} : Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(5) During communication at same potential (simplified I²C mode) (1/2) $(T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCL _r clock frequency	f _{SCL}	2.7 V \leq EV _{DD0} \leq 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ		1000 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ		400 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V \leq EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
		1.7 V \leq EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ		250 Note 1		250 Note 1		250 Note 1	kHz
		1.6 V \leq EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	—		250 Note 1		250 Note 1		kHz
Hold time when SCL _r = "L"	t _{LOW}	2.7 V \leq EV _{DD0} \leq 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1150		1150		ns
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1150		1150		1150		ns
		1.8 V \leq EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1550		1550		1550		ns
		1.7 V \leq EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	1850		1850		1850		ns
		1.6 V \leq EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	—		1850		1850		ns
Hold time when SCL _r = "H"	t _{HIGH}	2.7 V \leq EV _{DD0} \leq 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1150		1150		ns
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1150		1150		1150		ns
		1.8 V \leq EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1550		1550		1550		ns
		1.7 V \leq EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	1850		1850		1850		ns
		1.6 V \leq EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	—		1850		1850		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

UART mode bit width (during communication at different potential) (reference)

- Remarks**
1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,
 $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 3. f_{MCK} : Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

- (3) When reference voltage (+) = V_{DD} ($\text{ADREFP1} = 0$, $\text{ADREFP0} = 0$), reference voltage (-) = V_{SS} ($\text{ADREFM} = 0$), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+85^\circ\text{C}$, $1.6 \text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 \text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0 \text{ V}$, Reference voltage (+) = V_{DD} , Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$		1.2	± 7.0	LSB
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3		1.2	± 10.5	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	3.6 V $\leq V_{DD} \leq 5.5 \text{ V}$	2.125		39	μs
			2.7 V $\leq V_{DD} \leq 5.5 \text{ V}$	3.1875		39	μs
			1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$	17		39	μs
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$	57		95	μs
Conversion time	t _{CONV}	10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V $\leq V_{DD} \leq 5.5 \text{ V}$	2.375		39	μs
			2.7 V $\leq V_{DD} \leq 5.5 \text{ V}$	3.5625		39	μs
			2.4 V $\leq V_{DD} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 0.60	%FSR
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 0.85	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 0.60	%FSR
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 0.85	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 4.0	LSB
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 6.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	1.8 V $\leq V_{DD} \leq 5.5 \text{ V}$			± 2.0	LSB
			1.6 V $\leq V_{DD} \leq 5.5 \text{ V}$ Note 3			± 2.5	LSB
Analog input voltage	V _{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI26		0		EV_{DD0}	V
		Internal reference voltage (2.4 V $\leq V_{DD} \leq 5.5 \text{ V}$, HS (high-speed main) mode)		V_{BGR} ^{Note 4}			V
		Temperature sensor output voltage (2.4 V $\leq V_{DD} \leq 5.5 \text{ V}$, HS (high-speed main) mode)		V_{TMPS25} ^{Note 4}			V

- Notes**
- Excludes quantization error ($\pm 1/2$ LSB).
 - This value is indicated as a ratio (%FSR) to the full-scale value.
 - When the conversion time is set to 57 μs (min.) and 95 μs (max.).
 - Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

Notes 1. Total current flowing into V_{DD} and EV_{DD0} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} or V_{SS} , EV_{SS0} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.
3. When high-speed on-chip oscillator and subsystem clock are stopped.
4. When high-speed system clock and subsystem clock are stopped.
5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
HS (high-speed main) mode: $2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @1 MHz to 32 MHz
 $2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$ @1 MHz to 16 MHz
8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remarks 1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
2. f_{IH} : High-speed on-chip oscillator clock frequency
3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^\circ\text{C}$

(3) Peripheral Functions (Common to all products)(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I _{FIL} Note 1				0.20		µA
RTC operating current	I _{RTC} Notes 1, 2, 3				0.02		µA
12-bit interval timer operating current	I _{IT} Notes 1, 2, 4				0.02		µA
Watchdog timer operating current	I _{WDT} Notes 1, 2, 5	f _{IL} = 15 kHz			0.22		µA
A/D converter operating current	I _{ADC} Notes 1, 6	When conversion at maximum speed	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
			Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	I _{ADREF} Note 1				75.0		µA
Temperature sensor operating current	I _{TMPS} Note 1				75.0		µA
LVD operating current	I _{LVD} Notes 1, 7				0.08		µA
Self programming operating current	I _{FSP} Notes 1, 9				2.50	12.20	mA
BGO operating current	I _{BGO} Notes 1, 8				2.50	12.20	mA
SNOOZE operating current	I _{SNOZ} Note 1	ADC operation	The mode is performed ^{Note 10}		0.50	1.10	mA
			The A/D conversion operations are performed, Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		1.20	2.04	mA
		CSI/UART operation			0.70	1.54	mA

Notes 1. Current flowing to the V_{DD}.

2. When high speed on-chip oscillator and high-speed system clock are stopped.
3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{RTC}, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of the real-time clock.
4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.
5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer operates.

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode	Unit
		MIN.	MAX.		
Transfer rate	Reception	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	Theoretical value of the maximum transfer rate f _{CLK} = 32 MHz, f _{MCK} = f _{CLK}	f _{MCK} /12 ^{Note 1}	bps
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	Theoretical value of the maximum transfer rate f _{CLK} = 32 MHz, f _{MCK} = f _{CLK}	f _{MCK} /12 ^{Note 1}	Mbps
		2.4 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V	Theoretical value of the maximum transfer rate f _{CLK} = 32 MHz, f _{MCK} = f _{CLK}	f _{MCK} /12 ^{Notes 1,2}	bps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The following conditions are required for low voltage interface when EV_{DD0} < V_{DD}.
2.4 V ≤ EV_{DD0} < 2.7 V : MAX. 1.3 Mbps

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

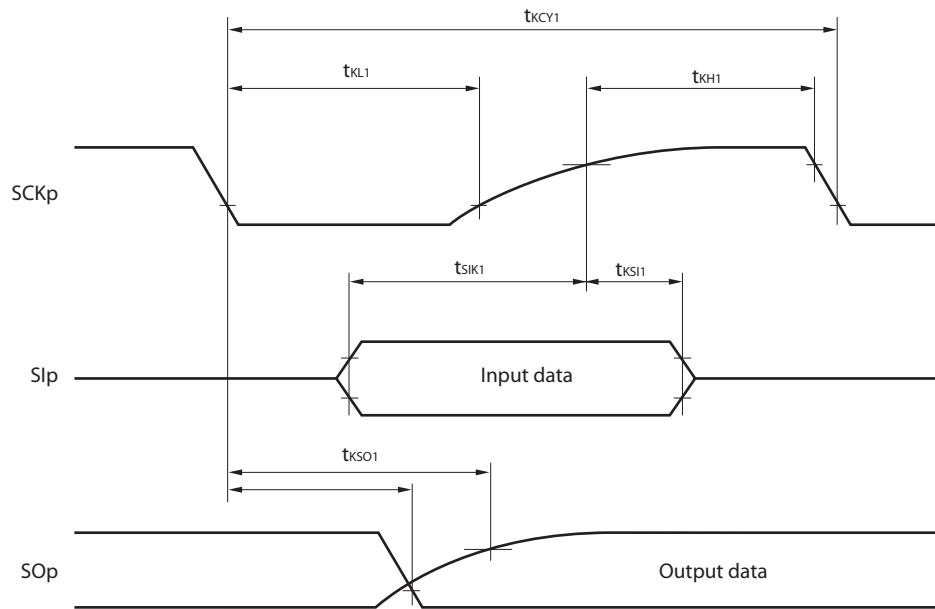
3. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

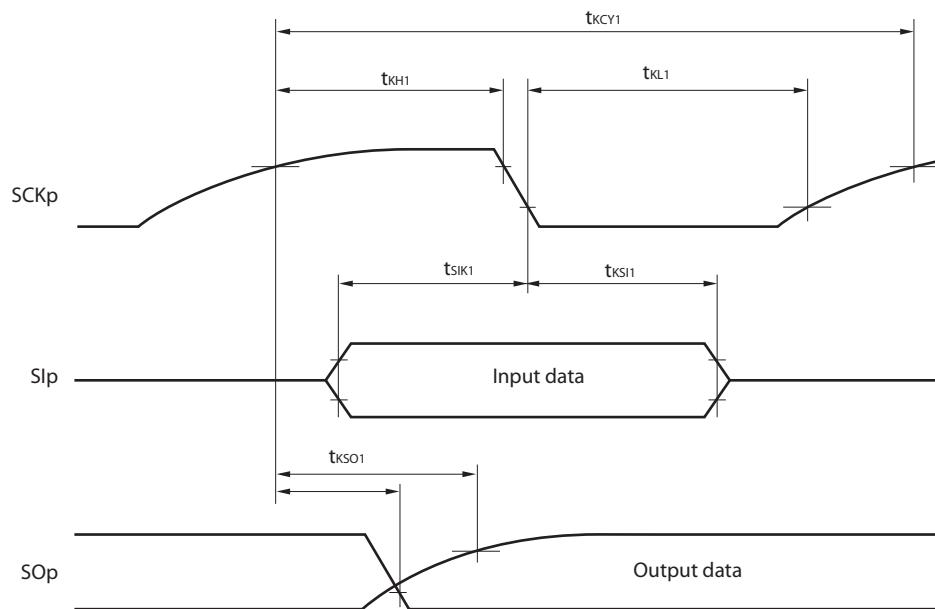
4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

CSI mode serial transfer timing (master mode) (during communication at different potential)

(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

**CSI mode serial transfer timing (master mode) (during communication at different potential)**

(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 00, 01, 02, 10, 12, 13), n: Channel number (n = 0, 2), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

- (3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB
Conversion time	t _{CONV}	10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
		Target pin: ANI0 to ANI14, ANI16 to ANI26	2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
		2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs	
		10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625		39	μs
		2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs	
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±4.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±2.0	LSB
Analog input voltage	V _{AIN}	ANI0 to ANI14		0		V _{DD}	V
		ANI16 to ANI26		0		EV _{DD0}	V
		Internal reference voltage output (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)			V _{BGR} ^{Note 3}		V
		Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)			V _{TMP525} ^{Note 3}		V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

3.6.5 Power supply voltage rising slope characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $V_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

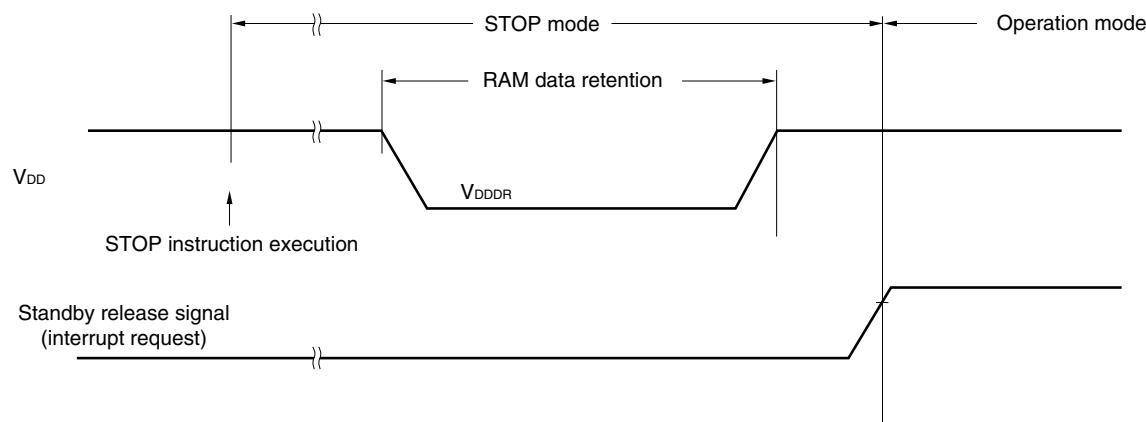
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $V_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.44 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.

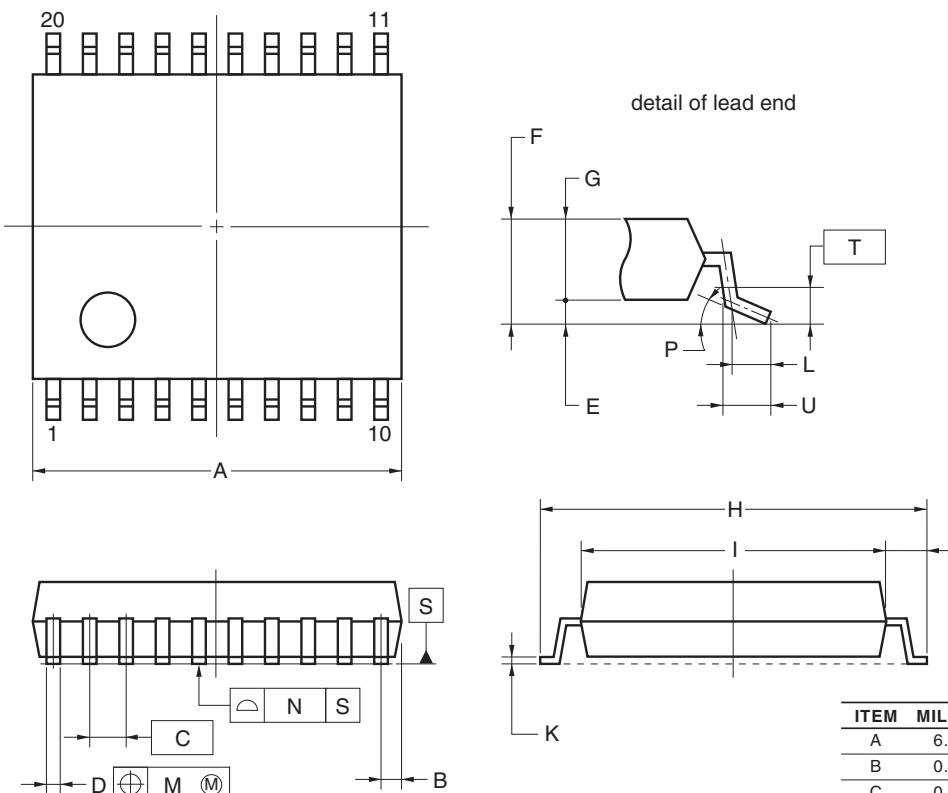


4. PACKAGE DRAWINGS

4.1 20-pin Products

R5F1006AASP, R5F1006CASP, R5F1006DASP, R5F1006EASP
 R5F1016AASP, R5F1016CASP, R5F1016DASP, R5F1016EASP
 R5F1006ADSP, R5F1006CDSP, R5F1006DDSP, R5F1006EDSP
 R5F1016ADSP, R5F1016CDSP, R5F1016DDSP, R5F1016EDSP
 R5F1006AGSP, R5F1006CGSP, R5F1006DGSP, R5F1006EGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-0300-0.65	PLSP0020JC-A	S20MC-65-5A4-3	0.12



NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

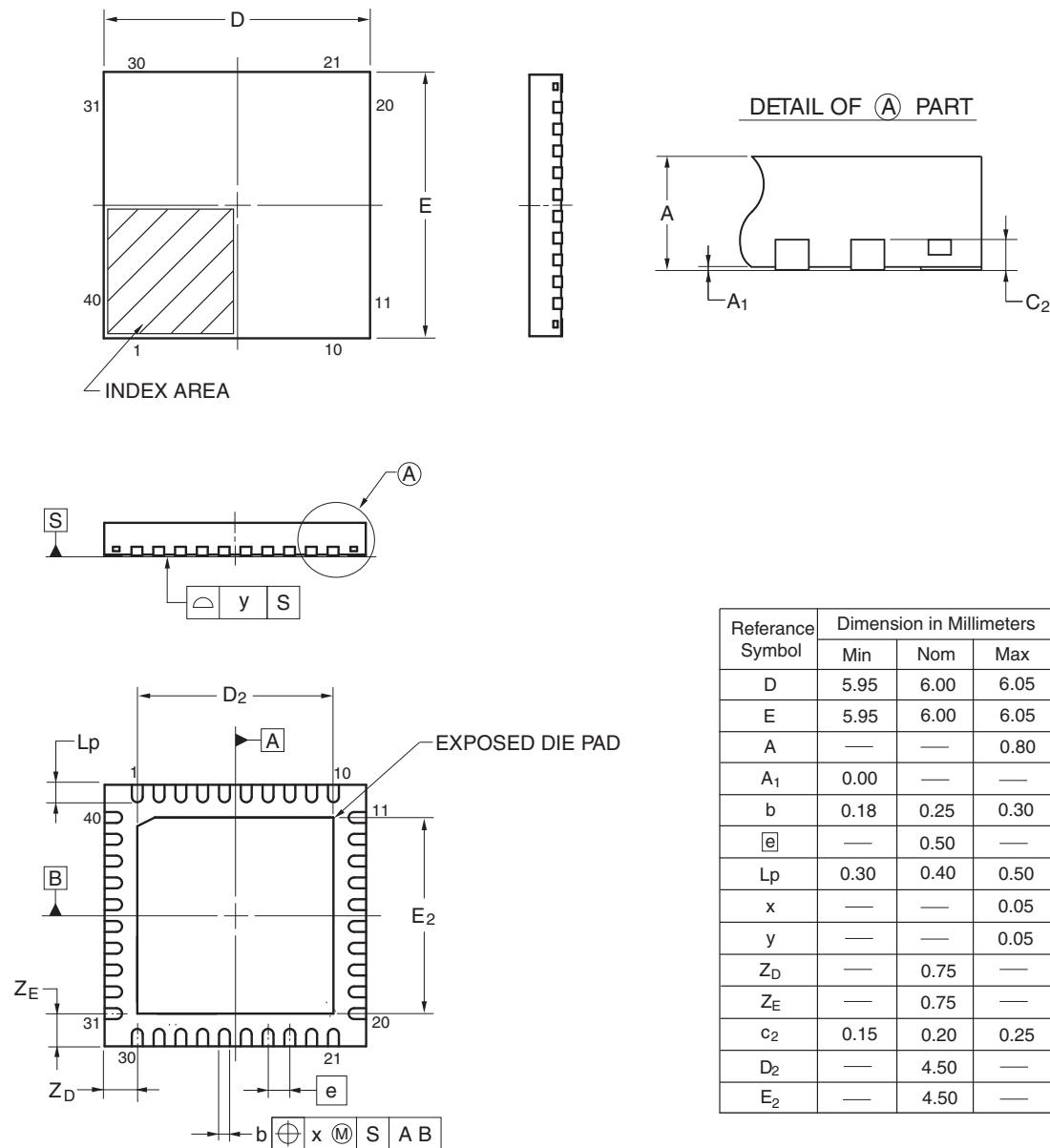
ITEM	MILLIMETERS
A	6.65±0.15
B	0.475 MAX.
C	0.65 (T.P.)
D	0.24 ^{+0.08} _{-0.07}
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	3° ^{+5°} _{-3°}
T	0.25
U	0.6±0.15

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4.7 40-pin Products

R5F100EAANA, R5F100ECANA, R5F100EDANA, R5F100EEANA, R5F100EFANA, R5F100EGANA, R5F100EHANA
 R5F101EAANA, R5F101ECANA, R5F101EDANA, R5F101EEANA, R5F101EFANA, R5F101EGANA, R5F101EHANA
 R5F100EADNA, R5F100ECDNA, R5F100EDDNA, R5F100EEDNA, R5F100EFDNA, R5F100EGDNA,
 R5F100EHDNA
 R5F101EADNA, R5F101ECDNA, R5F101EDDNA, R5F101EEDNA, R5F101EFDNA, R5F101EGDNA,
 R5F101EHDNA
 R5F100EAGNA, R5F100ECGNA, R5F100EDGNA, R5F100EEGNA, R5F100EFGNA, R5F100EGGNA,
 R5F100EHGNA

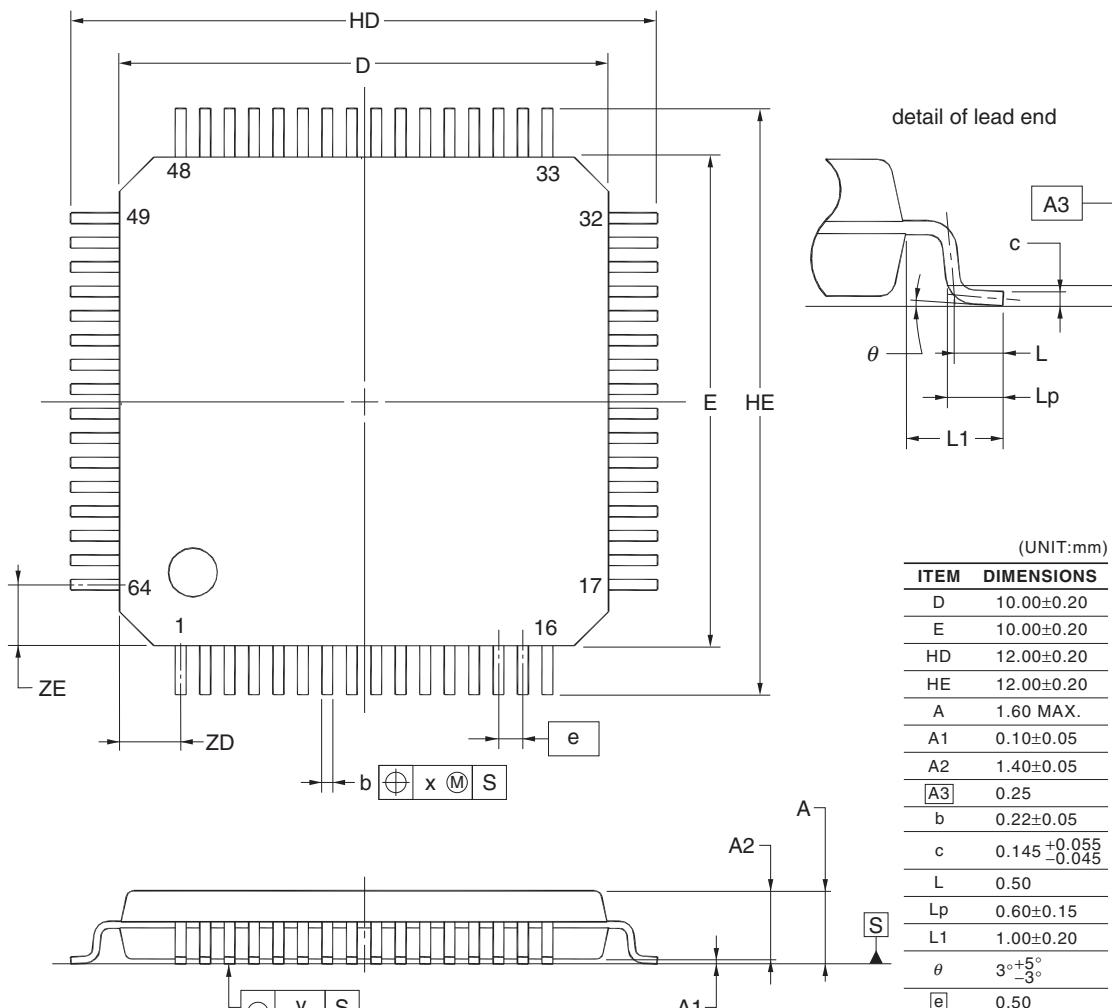
JEITA Package code	RENESAS code	Previous code	MASS (TYP) [g]
P-HWQFN40-6x6-0.50	PWQN0040KC-A	P40K8-50-4B4-5	0.09



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R5F100LCAF, R5F100LDAFB, R5F100LEAFB, R5F100LFAFB, R5F100LGAFB, R5F100LHAFB, R5F100LJAFB,
 R5F100LKAFB, R5F100LLAFB
 R5F101LCAF, R5F101LDAFB, R5F101LEAFB, R5F101LFAFB, R5F101LGAFB, R5F101LHAFB,
 R5F101LJAFB, R5F101LKAFB, R5F101LLAFB
 R5F100LCDFB, R5F100LDDFB, R5F100LEDFB, R5F100LFDFB, R5F100LGDFB, R5F100LHDFB, R5F100LJDFB,
 R5F100LKDFB, R5F100LLDFB
 R5F101LCDFB, R5F101LDDFB, R5F101LEDFB, R5F101LFDFB, R5F101LGDFB, R5F101LHDFB,
 R5F101LJDFB, R5F101LKDFB, R5F101LLDFB
 R5F100LCGFB, R5F100LDGFB, R5F100LEGFB, R5F100LFGFB, R5F100LGGFB, R5F100LHGFB,
 R5F100LJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP64-10x10-0.50	PLQP0064KF-A	P64GB-50-UEU-2	0.35

**NOTE**

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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Rev.	Date	Description	
		Page	Summary
3.00	Aug 02, 2013	81	Modification of figure of AC Timing Test Points
		81	Modification of description and note 3 in (1) During communication at same potential (UART mode)
		83	Modification of description in (2) During communication at same potential (CSI mode)
		84	Modification of description in (3) During communication at same potential (CSI mode)
		85	Modification of description in (4) During communication at same potential (CSI mode) (1/2)
		86	Modification of description in (4) During communication at same potential (CSI mode) (2/2)
		88	Modification of table in (5) During communication at same potential (simplified I ² C mode) (1/2)
		89	Modification of table and caution in (5) During communication at same potential (simplified I ² C mode) (2/2)
		91	Modification of table and notes 1 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		92, 93	Modification of table and notes 2 to 7 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		94	Modification of remarks 1 to 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		95	Modification of table in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (1/2)
		96	Modification of table and caution in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (2/2)
		97	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		98	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		99	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		100	Modification of remarks 3 and 4 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		102	Modification of table in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/2)
		103	Modification of table and caution in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/2)
		106	Modification of table in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (1/2)
		107	Modification of table, note 1, and caution in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (2/2)
		109	Addition of (1) I ² C standard mode
		111	Addition of (2) I ² C fast mode
		112	Addition of (3) I ² C fast mode plus
		112	Modification of IICA serial transfer timing
		113	Addition of table in 2.6.1 A/D converter characteristics
		113	Modification of description in 2.6.1 (1)
		114	Modification of notes 3 to 5 in 2.6.1 (1)
		115	Modification of description and notes 2, 4, and 5 in 2.6.1 (2)
		116	Modification of description and notes 3 and 4 in 2.6.1 (3)
		117	Modification of description and notes 3 and 4 in 2.6.1 (4)

Rev.	Date	Description	
		Page	Summary
3.00	Aug 02, 2013	118	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics
		118	Modification of table and note in 2.6.3 POR circuit characteristics
		119	Modification of table in 2.6.4 LVD circuit characteristics
		120	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode
		120	Renamed to 2.6.5 Power supply voltage rising slope characteristics
		122	Modification of table, figure, and remark in 2.10 Timing Specs for Switching Flash Memory Programming Modes
		123	Modification of caution 1 and description
		124	Modification of table and remark 3 in Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)
		126	Modification of table, note, caution, and remark in 3.2.1 X1, XT1 oscillator characteristics
		126	Modification of table in 3.2.2 On-chip oscillator characteristics
		127	Modification of note 3 in 3.3.1 Pin characteristics (1/5)
		128	Modification of note 3 in 3.3.1 Pin characteristics (2/5)
		133	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (1/2)
		135	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (2/2)
		137	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (1/2)
		139	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (2/2)
		140	Modification of (3) Peripheral Functions (Common to all products)
		142	Modification of table in 3.4 AC Characteristics
		143	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		143	Modification of figure of AC Timing Test Points
		143	Modification of figure of External System Clock Timing
		145	Modification of figure of AC Timing Test Points
		145	Modification of description, note 1, and caution in (1) During communication at same potential (UART mode)
		146	Modification of description in (2) During communication at same potential (CSI mode)
		147	Modification of description in (3) During communication at same potential (CSI mode)
		149	Modification of table, note 1, and caution in (4) During communication at same potential (simplified I ² C mode)
		151	Modification of table, note 1, and caution in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		152 to 154	Modification of table, notes 2 to 6, caution, and remarks 1 to 4 in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		155	Modification of table in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		156	Modification of table and caution in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		157, 158	Modification of table, caution, and remarks 3 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		160, 161	Modification of table and caution in (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)